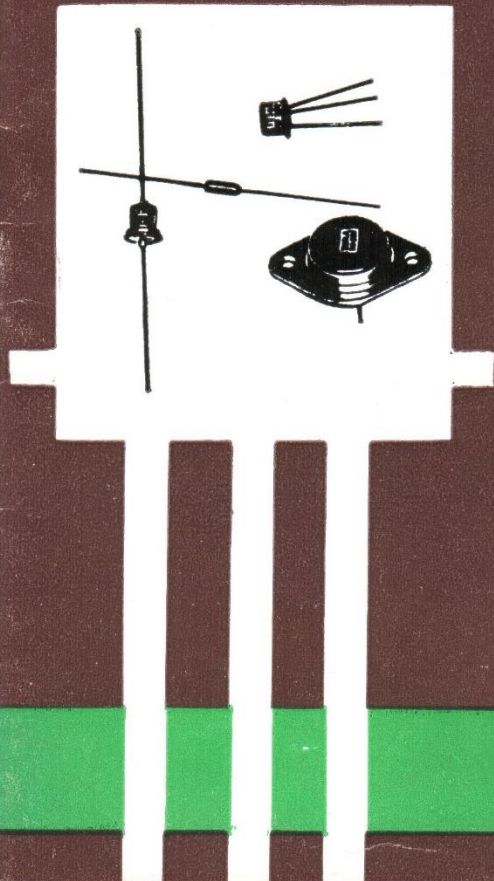


**TESLA**

842 133

**SEMI-CONDUCTORS  
HALBLEITER-BAUELEMENTE**



1975

**SILICON R. F. AND SWITCHING TRANSISTORS N-P-N**  
**SILIZIUM HF- UND SCHALT-TRANSISTOREN N-P-N**

Type Typ	$I_{CBO}$ at bei $U_{CB}$ $\mu A$	$U_{CB}$ V	$h_{21E}$ at bei $ h_{21e} ^*$ V	$I_E$ mA	$f$ MHz	$f_T$ MHz	Maximum ratings Grenzdaten						
							$U_{CBO}$ V	$U_{CER}$ V	$I_C$ mA	$U_{EBD}$ V	$P_C^{(7)}$ mW	$T_j$ °C	
KF124	0,0008	10	67...220	10	-1	—	350	30	20	30	5	220	125
KF125	0,0008	10	37...125	10	-1	—	230	30	20	30	5	220	125
KF167	0,3	30	> 26	9	-4	—	> 250	40	30	25	4	130	175
KF173	0,3	30	> 38	9	-7	—	> 400	40	25	25	4	200	175
KF503	0,5	50	100	10	-30	—	—	100 <sup>2)</sup>	50	5	700 <sup>3)</sup>	175	
KF504	0,1	140	> 3*	10	-10	30	150	160 <sup>2)</sup>	50	5	700 <sup>3)</sup>	175	
			> 3*	10	-10	30	150						
KF506	0,01	60	35—125	10	-10	—	—	75	50 <sup>5)</sup>	500	7	800	200
				10	-50	30	> 60						
KF507	0,5	30	> 35	10	-10	—	—	40	32 <sup>5)</sup>	500	5	800	200
				10	-50	30	> 50						
KF508	0,01	60	90—300	10	-10	—	—	75	50 <sup>5)</sup>	500	7	800	200
				10	-50	30	> 70						
KF524	0,0008	10	67...220	10	-1	—	350	30	20	30	5	145	175
KF525	0,0008	10	37...125	10	-1	—	300	30	20	30	5	145	175
KS500	0,5	15	> 20	1	-10	—	—	25	14	200	5	1000 <sup>10)</sup> 6)	200
				10	-10	> 200	300						

- 1)  $U_{CB} = 10$  V,  $I_E = 10$  mA,  $f = 2$  MHz  
 2)  $R_{BE} = 0$   $\Omega$   
 3) With ideal cooling 2500 mW  
 Mit idealer Kühlung 2500 mW  
 4)  $U_{CB} = 10$  V,  $I_E = 10$  mA,  $f = 2$  MHz  
 5)  $R_{BE} = 500$   $\Omega$   
 6) With ideal cooling  
 Mit idealer Kühlung  
 7)  $T_a = 25$  °C  
 10)  $T_C < 45$  °C

**SILICON TRANSISTORS P-N-P**  
**SILIZIUM TRANSISTOREN P-N-P**

Type Typ	$I_{CBO}$ at bei $U_{CB}$ $\mu A$	$U_{CB}$ V	$h_{21E}$ at bei $ h_{21e} ^*$ V	$I_E$ mA	$f$ MHz	$U_{CES}$ max V	Maximum ratings Grenzdaten					
							$U_{CBO}$ V	$U_{CER}$ V	$I_C$ mA	$U_{EBO}$ V	$P_{tot}$ mW	$T_j$ °C
KF517	-0,50	-30	> 2*	-10	50	30	-40	-30 <sup>1)</sup>	-600	-5	800	200
KF517A KF517B			> 35	-10	10	—					2600 <sup>2)</sup>	
			35...120	-10	10	—						
			90...300	-10	10	—						

- 1)  $R_{BE} < 10$   $\Omega$       2) With ideal cooling      • Mit idealer Kühlung

**MOS FIELD EFFECT TRANSISTORS**  
**MOS FELDEFFEKT-TRANSISTOREN**

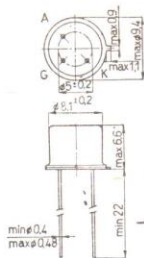
Type Typ	$R_{dst}$ $\Omega$	$y_{21}$ at bei mS	$U_{CE}$ V	$I_C$ mA	$U_{GE}$ V	$C_{vst}$ pF	Maximum ratings Grenzdaten					
							$U_{CE}$ V	$U_{GE}$ V	$I_C$ mA	$P_{tot}$ mW	$T_j$ °C	Channel Kanal
KF520	> 10 <sup>13</sup>	> 0,3	15	5	0	8	30	$\pm 70$ <sup>1)</sup>	30	300	175	N
KF521		3,5 > 2,5	6	4...11	0	5	20 <sup>2)</sup>	$\pm 20$ <sup>3)</sup>	10	100	150	N

- 1)  $U_{CE} = 15$  V      2)  $U_{G1E} = -6$  V      3)  $U_{G1EO}$

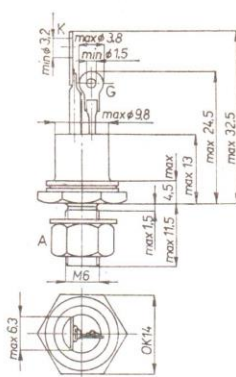
**DUAL MOS FIELD EFFECT TRANSISTOR WITH CHANNEL P**  
**DOPPEL-MOS-FELDEFFEKT TRANSISTOR MIT KANAL P**

Type Typ	$-U_{GET}$ at bei V	$-U_{GE}$ V	$I_{CE}$ $\mu A$	$\Delta U_{GET}$ V	$r_{CE(ON)}$ k $\Omega$	$r_{CE(OFF)}$ M $\Omega$	Maximum ratings Grenzdaten				
							$-U_{CEM}$ V	$-U_{GEM}$ V	$-U_{GCM}$ V	$-I_{CEM}$ mA	$P_{tot}$ mW
KF552	2...6	$= -U_C$	10	< 0,5	—	—	10	30	30	15	100
		7			< 1 <sup>1)</sup>	—					
		2			—	> 100 <sup>1)</sup>					

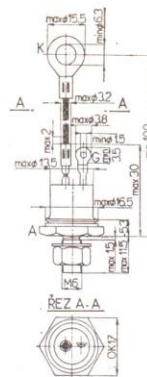
- 1)  $f = 10$  kHz



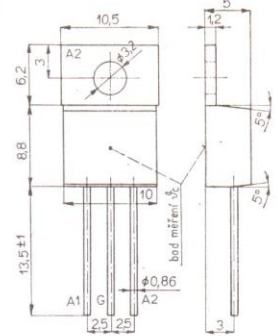
KT501-KT505  
KT506 L = max. 21 mm  
KT508 L = min. 19 mm



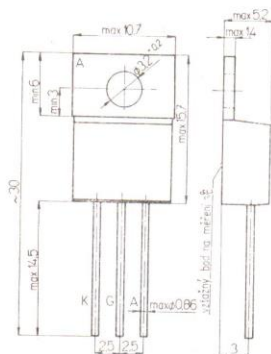
KT710-KT714



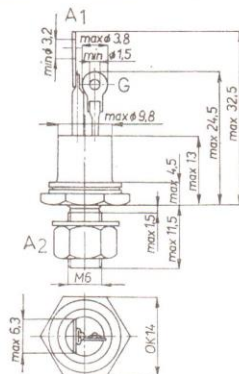
KT701-KT705



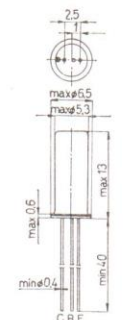
KT205/200  
KT205/400  
KT205/600



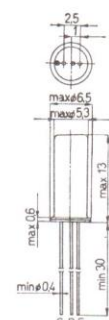
KT206



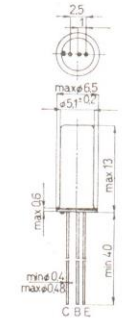
KT772-KT774  
KT782-KT784



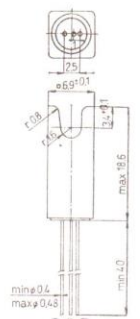
101NU70 - 156NU70  
101NU71 - 104NU71



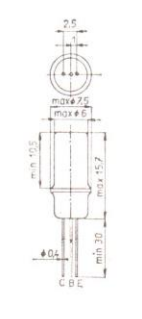
GS507



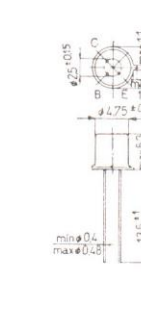
GC500-GC502  
(new design)  
GC510-GC512  
GC520-GC522



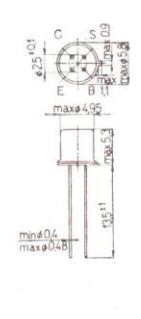
GC510K-GC512K  
GC520K-GC522K



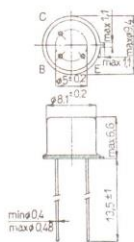
GC500 - GC502  
(old design)



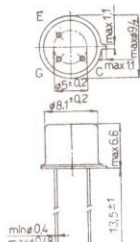
KC507-KC509  
KS500  
KSY62, KSY63  
KSY21, KSY71, KSY82  
TR12, TR15



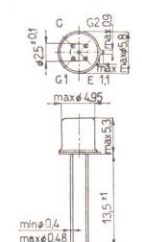
KF167  
KF173  
KF524, KF525



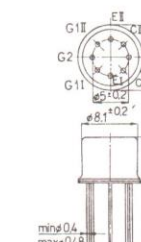
KF503-KF504  
KF506-KF508  
KF517  
KFY16, KFY18  
KFY34, KFY46



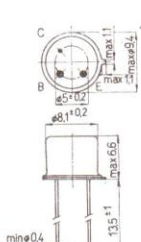
KF520



KF521



KF552



KSY34